

## ABSTRACT

### 5     PROCESS FOR THE FABRICATING AN ELECTRONIC INTEGRATED CIRCUIT AND ELECTRONIC INTEGRATED CIRCUIT THUS OBTAINED

10         A process for fabricating an electronic  
integrated circuit comprises the formation on a  
substrate (100), of which a part is composed of  
absorbing material, of a portion (1) made of a  
sacrificial material. The sacrificial material includes  
cobalt, nickel, titanium, tantalum, tungsten,  
15 molybdenum, gallium, indium, silver, gold, iron and/or  
chromium. A rigid portion (3,4) is formed in fixed  
contact with the substrate, on one side of the portion  
of sacrificial material (1) opposite to the part of the  
substrate composed of absorbing material. The circuit  
20 is heated such that the sacrificial material is  
absorbed into the part of the substrate composed of  
absorbing material. A substantially empty volume (V) is  
thus created in place of the portion of sacrificial  
material (1). Said volume that is substantially empty  
25 can replace a dielectric material situated between the  
electrodes of a capacitor.

Figure 4